

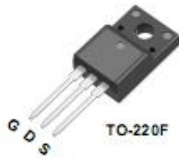
650V N-Channel Multi-EPI Super-JMOSFET

General Description

This Power MOSFET is produced using Silkor's advanced Superjunction MOSFET technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies.

Features

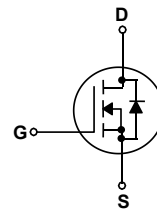
- 8A, 650V, $R_{DS(on)Typ} = 550m\Omega @ V_{GS} = 10V$
- Low gate charge (typ. $Q_g = 10.1nC$)
- High ruggedness
- Ultra fast switching
- 100% avalanche tested
- Improved dv/dt capability



SL8N65CF



SL8N65CD



Absolute Maximum Ratings

$T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	SL8N65CF/SL8N65CD		Units
V _{DSS}	Drain-Source Voltage	650		V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	8*		A
		4.8*		A
I _{DM}	Drain Current - Pulsed (Note 1)	24*		A
V _{GSS}	Gate-Source Voltage	±30		V
EAS	Single Pulsed Avalanche Energy (Note 2)	156		mJ
I _{AR}	Avalanche Current (Note 1)	1.9		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	0.61		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	20		V/ns
	MOSFET dv/dt	100		
P _D	Power Dissipation (T _C = 25°C)	24	69	W
	- Derate above 25°C	0.19	0.56	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	260		°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	SL8N65CF/SL8N65CD		Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	5.2	1.8	$^\circ C/W$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	-	-	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ C/W$

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	650	--	--	V
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}, T_J = 150^\circ\text{C}$	650	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	--	2.1	--	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	--	4.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$	--	550	600	m Ω

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{MHz}$	--	383	--	pF
C_{oss}	Output Capacitance		--	20	--	pF
C_{rss}	Reverse Transfer Capacitance		--	--	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 400\text{ V}, I_D = 2.5\text{ A}, R_G = 10\ \Omega, V_{GS} = 10\text{ V}$ (Note 4, 5)	--	6	--	ns
t_r	Turn-On Rise Time		--	7	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	26	--	ns
t_f	Turn-Off Fall Time		--	13	--	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 2.5\text{ A}, V_{GS} = 10\text{ V}$ (Note 4, 5)	--	10.1	--	nC
Q_{gs}	Gate-Source Charge		--	2.1	--	nC
Q_{gd}	Gate-Drain Charge		--	4.9	--	nC
R_G	Gate Resistance	$f = 1\text{MHz}$		0.7		Ω

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	8	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	24	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.5A	--	--	1.2	V
t _{rr}	Reverse Recovery Time	V _{DD} = 400 V, I _S = 2.5A, dI _F / dt = 100 A/us (Note 4)	--	173	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.1	--	uC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 80\text{mH}, V_{DD} = 80\text{V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 2.5\text{ A}, dI/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq 400$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

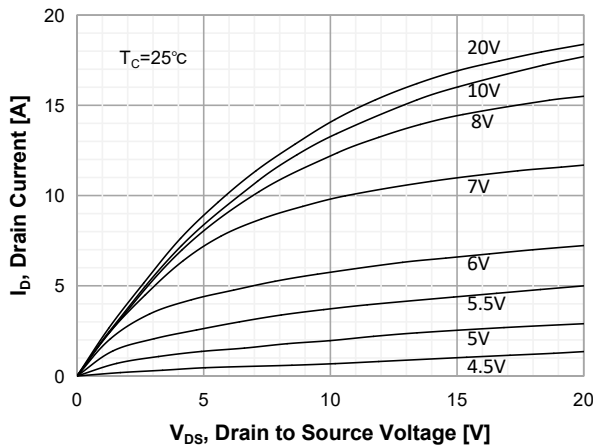


Figure 1. On-Region Characteristics

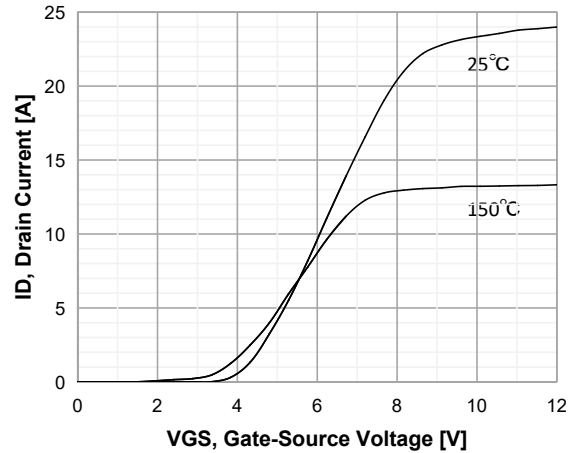


Figure 2. Transfer Characteristics

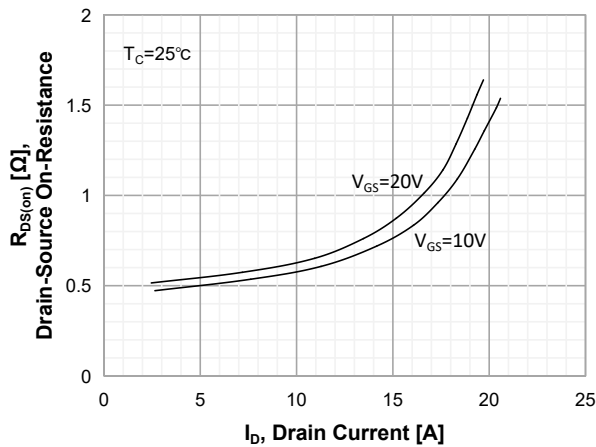


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

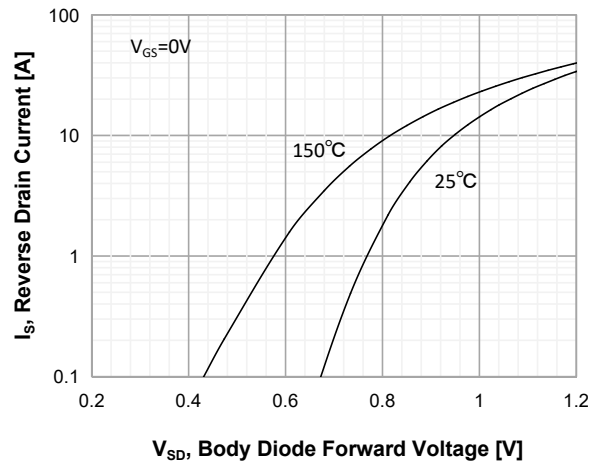


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

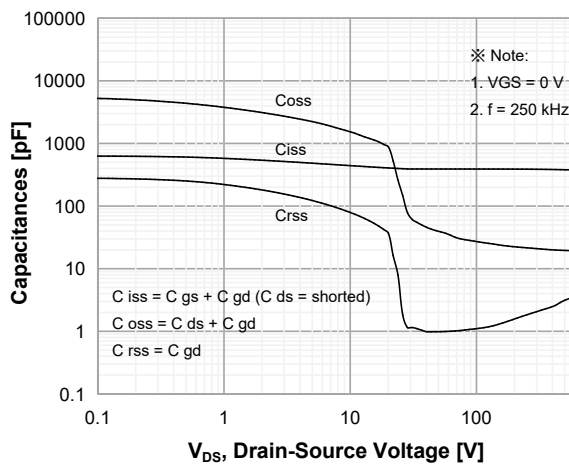


Figure 5. Capacitance Characteristics

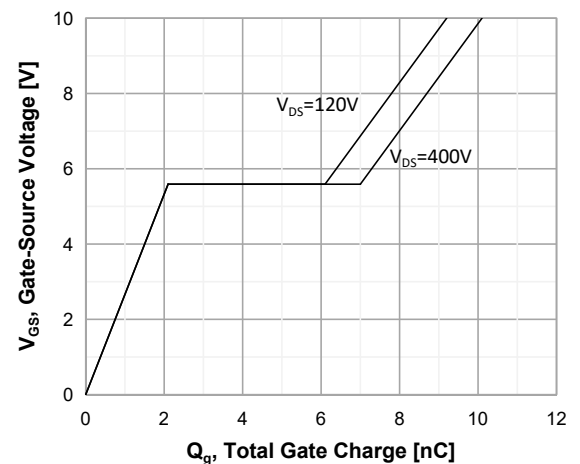


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

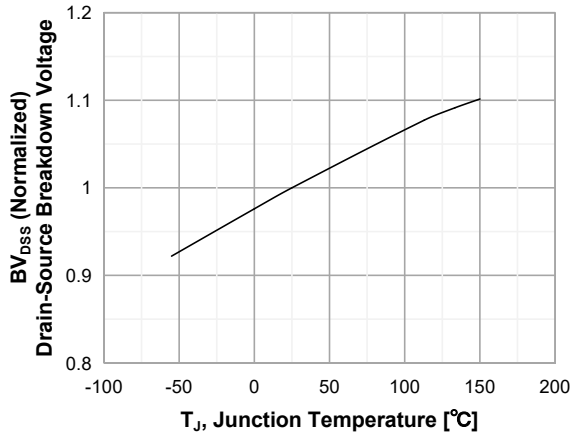


Figure 7. Breakdown Voltage Variation vs Temperature

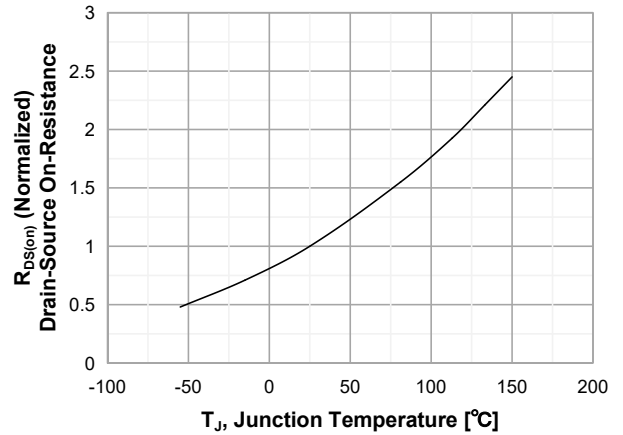


Figure 8. On-Resistance Variation vs Temperature

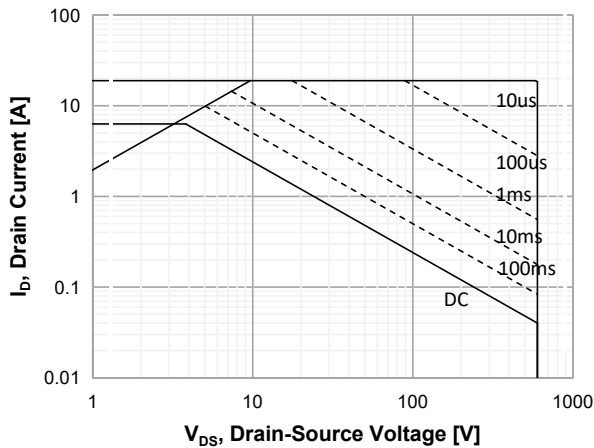


Figure 9. Maximum Safe Operating Area

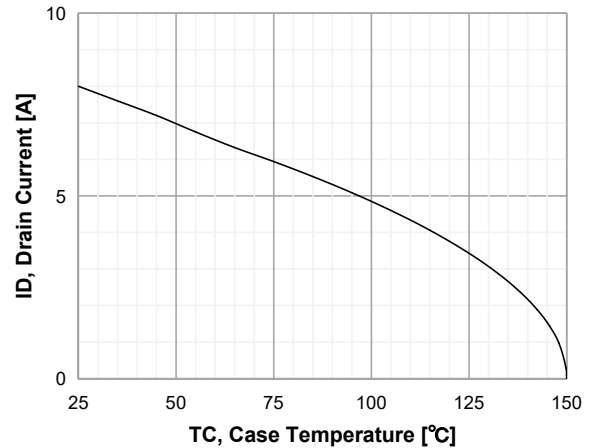


Figure 10. Maximum Drain Current vs. Case Temperature

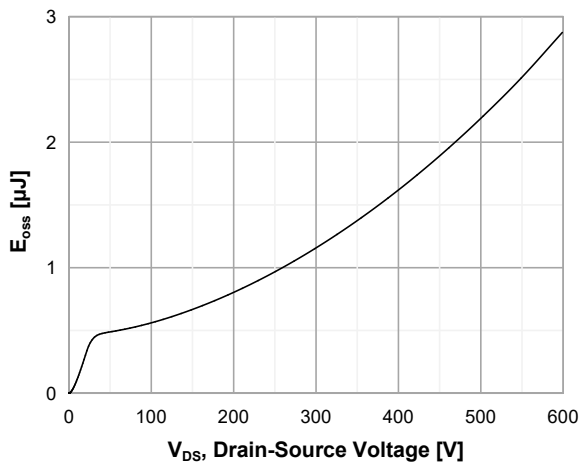


Figure 11. E_{oss} vs. Drain to Source Voltage

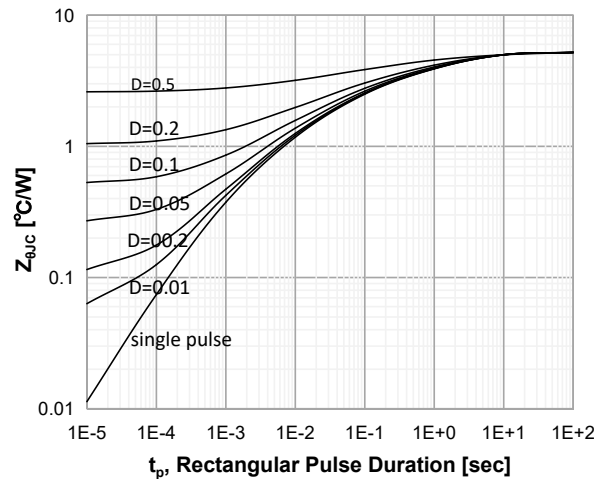
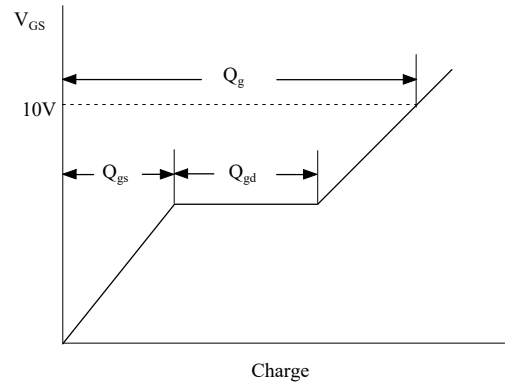
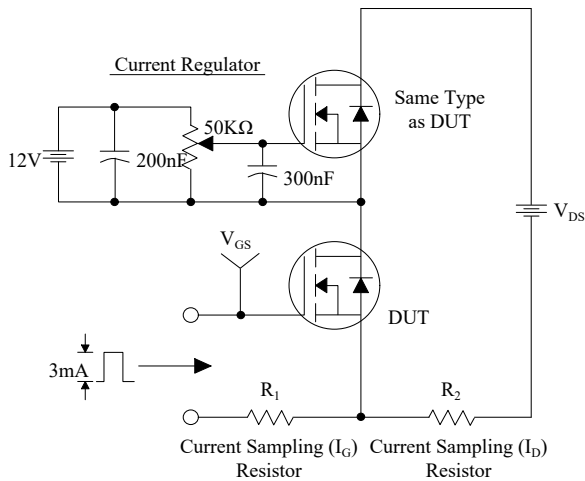
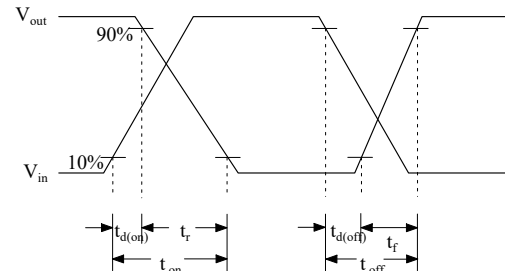
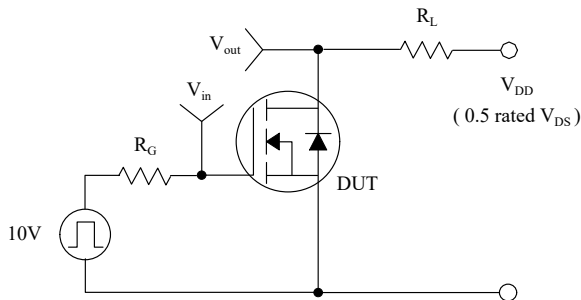


Figure 12. Transient Thermal Response Curve

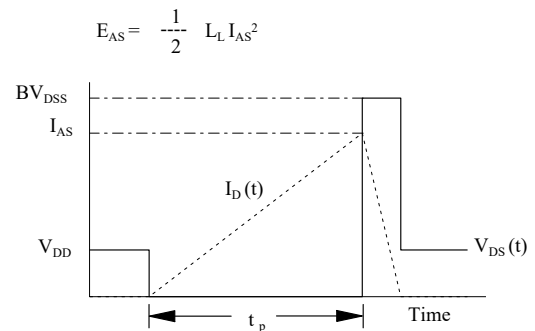
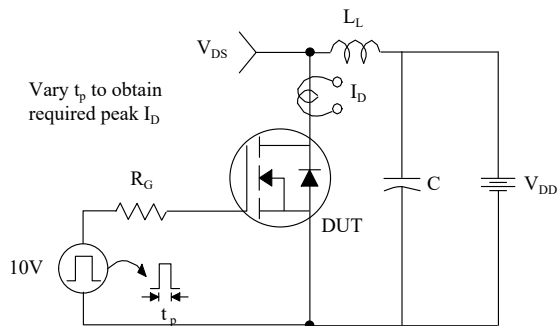
Gate Charge Test Circuit & Waveform



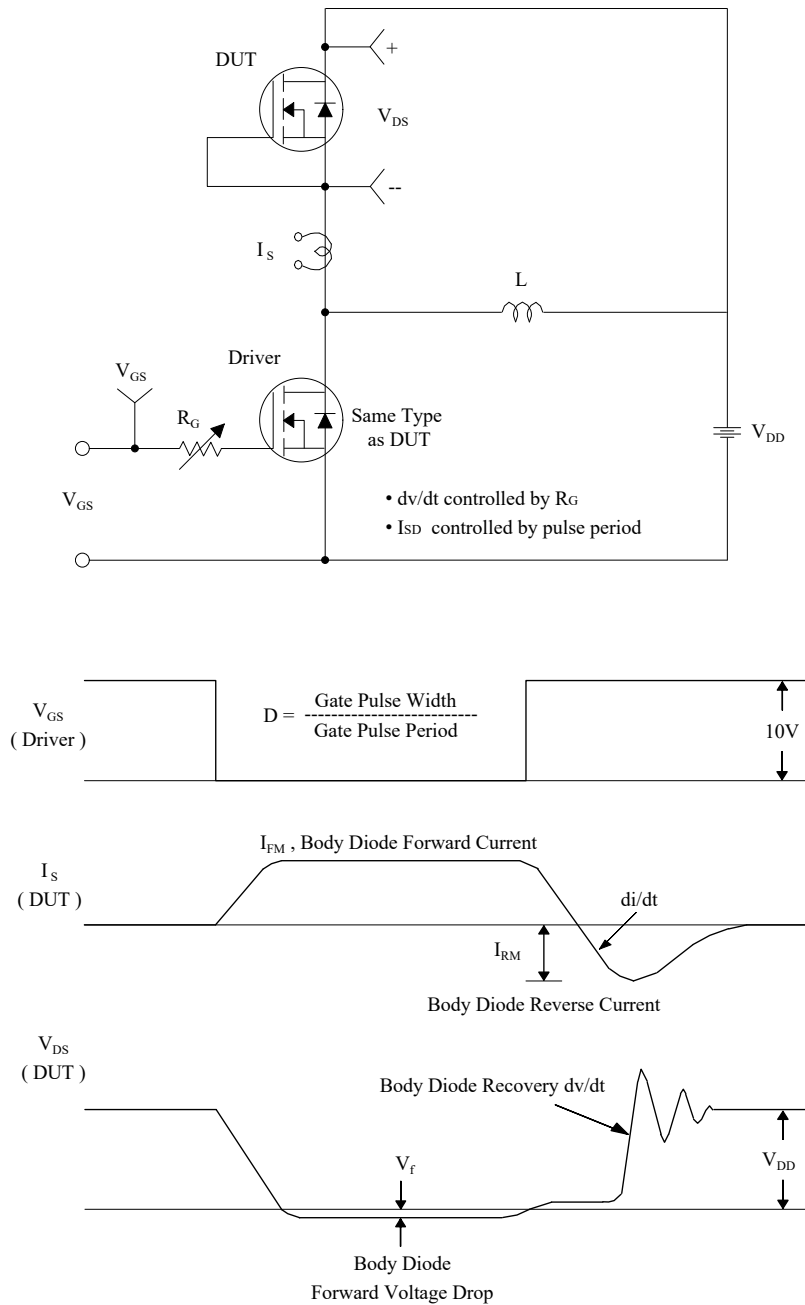
Resistive Switching Test Circuit & Waveforms



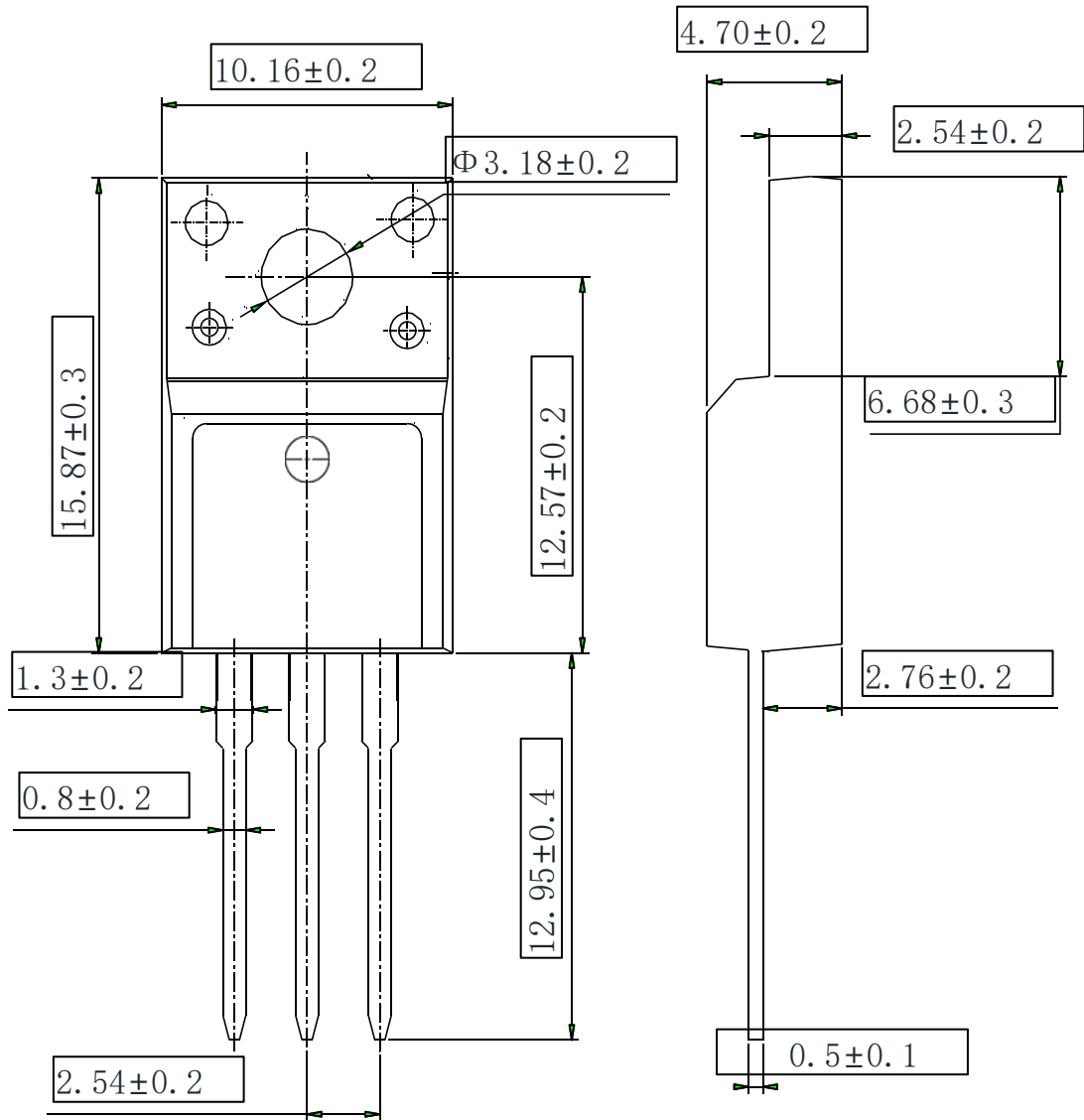
Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



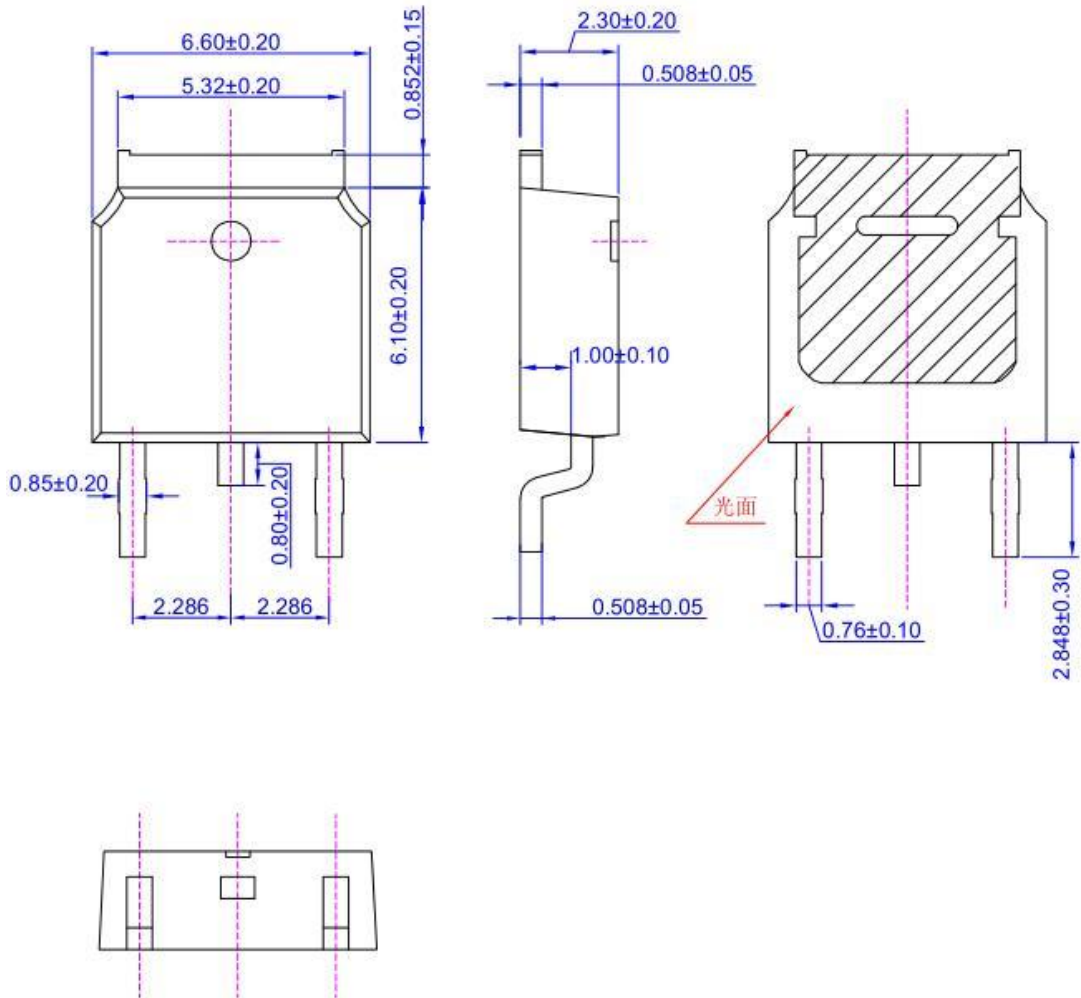
TO-220F OUTLINE



NOTE:

- 1The plastic package is not marked as smooth surface $R_a=0.1$; Subglossy surface $R_a=0.8$
- 2.Undeclared tolerance ± 0.15 , Unmarked fillet $R_{max}=0.25$

TO-252 OUTLINE



NOTE:

- 1The plastic package is not marked as smooth surface $R_a=0.1$; Subglossy surface $R_a=0.8$
- 2.Undeclared tolerance ± 0.25 , Unmarked fillet $R_{max}=0.25$